



DualCool™ N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16407Q5C

FEATURES

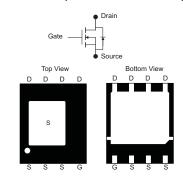
- Ultralow Q_q and Q_{qd}
- DualCool™ Package
- · Optimized for Two Sided Cooling
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

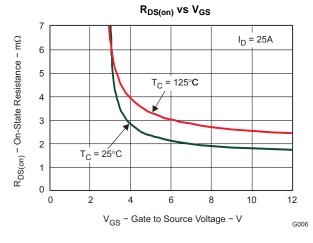
APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage 25			V
Q_g	Gate Charge Total (4.5V) 13.3			nC
Q_{gd}	Gate Charge Gate to Drain	3.5		nC
Б	Design to Course On Design	V _{GS} = 4.5V	2.5	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V	1.8	mΩ
V _(th)	Threshold Voltage	1.6		V

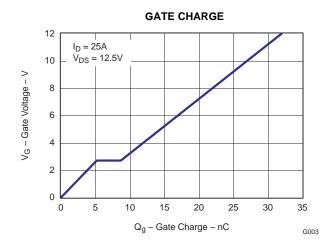
ORDERING INFORMATION

Device	Package	Media	Qty	Ship	
CSD16407Q5C	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel	

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	٧
V_{GS}	Gate to Source Voltage	+16 / -12	V
	Continuous Drain Current, T _C = 25°C	100	Α
I _D	Continuous Drain Current ⁽¹⁾	31	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	200	Α
P_D	Power Dissipation ⁽¹⁾	3.1	W
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D = 66A$, $L = 0.1mH$, $R_G = 25\Omega$	218	mJ

- (1) Typical $R_{\theta JA}=40^{\circ}\text{C/W}$ on 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

T_A = 25°C, unless otherwise specified

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics	•	•			
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V$, $V_{DS} = 20V$			1	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16V / -12V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	1.3	1.6	1.9	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 25A$		2.5	3.3	$m\Omega$
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 25A$		1.8	2.4	mΩ
9 _{fs}	Transconductance	$V_{DS} = 15V, I_D = 25A$		111		S
Dynamic	Characteristics					
C _{ISS}	Input Capacitance			2040	2660	pF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz$		1600	2080	pF
C _{RSS}	Reverse Transfer Capacitance			115	160	pF
R _g	Series Gate Resistance			1.2	2.4	Ω
Qg	Gate Charge Total (4.5V)			13.3	18	nC
Q _{gd}	Gate Charge Gate to Drain	V 40.5V I 05A		3.5		nC
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_{D} = 25A$		5.3		nC
Q _{g(th)}	Gate Charge at Vth			3.1		nC
Q _{OSS}	Output Charge	V _{DS} = 13.5V, V _{GS} = 0V		33		nC
t _{d(on)}	Turn On Delay Time			11.9		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$		18.4		ns
t _{d(off)}	Turn Off Delay Time	$I_D = 25A$, $R_G = 2\Omega$		16		ns
t _f	Fall Time			9		ns
Diode C	haracteristics		•			
V_{SD}	Diode Forward Voltage	I _S = 25A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	$V_{DD} = 13.5V$, $I_F = 25A$, $di/dt = 300A/\mu s$		42		nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13.5V$, $I_F = 25A$, $di/dt = 300A/\mu s$		34		ns

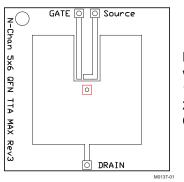
THERMAL CHARACTERISTICS

T_A = 25°C, unless otherwise specified

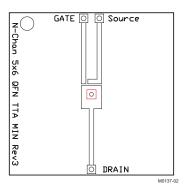
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (Top Source) ⁽¹⁾			1.2	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case (Bottom Drain) ⁽¹⁾			1.1	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			51	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 51^{\circ} C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 121^{\circ} C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $T_A = 25$ °C, unless otherwise specified

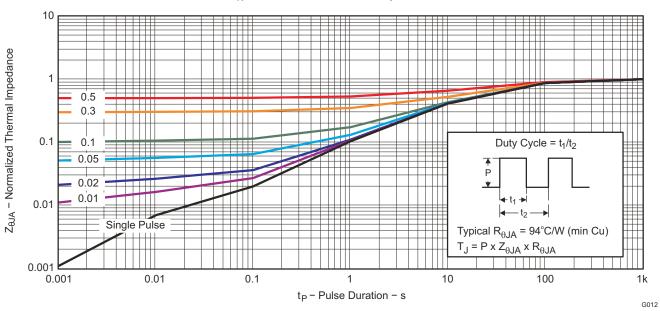


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

T_A = 25°C, unless otherwise specified

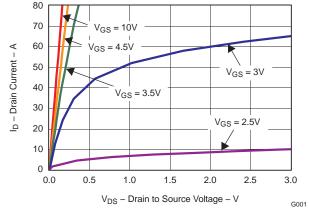


Figure 2. Saturation Characteristics

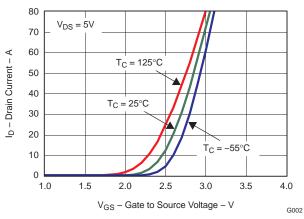


Figure 3. Transfer Characteristics

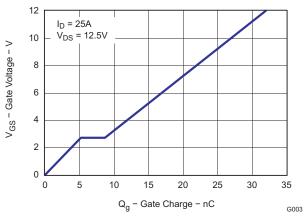


Figure 4. Gate Charge

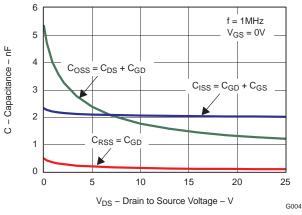


Figure 5. Capacitance

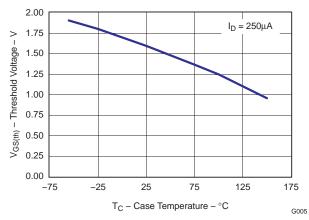


Figure 6. Threshold Voltage vs. Temperature

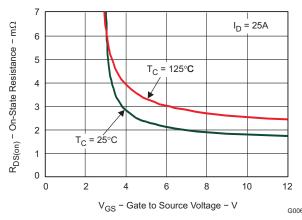


Figure 7. On-State Resistance vs. Gate to Source Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

$T_A = 25$ °C, unless otherwise specified

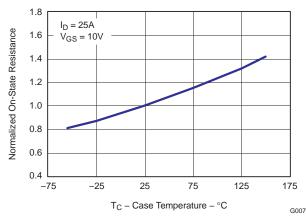


Figure 8. Normalized On-State Resistance vs. Temperature

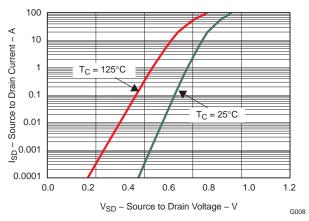


Figure 9. Typical Diode Forward Voltage

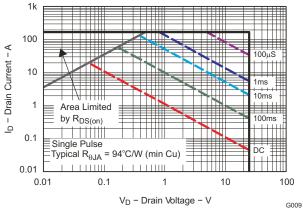


Figure 10. Maximum Safe Operating Area

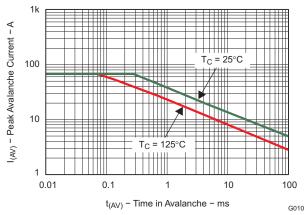


Figure 11. Single Pulse Unclamped Inductive Switching

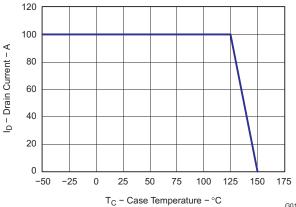
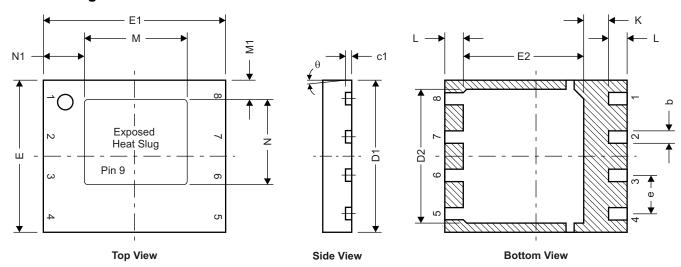


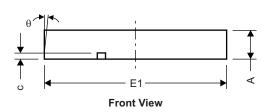
Figure 12. Maximum Drain Current vs. Temperature



MECHANICAL DATA

Q5C Package Dimensions



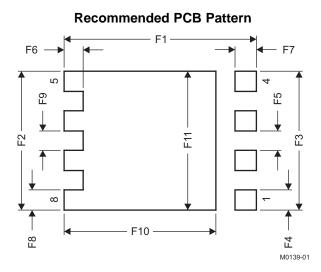


DualCool™Pinout				
Pin#	Label			
1, 2, 3, 9	Source			
4	Gate			
5, 6, 7, 8	Drain			

M0162-01

DIM	MILLIM	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
Е	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	TYP	0.050		
K	0.760	_	0.030	_	
L	0.510	0.710	0.020	0.028	
θ	-	-	_	_	
M	3.260	3.460	0.128	0.136	
M1	0.520	0.720	0.020	0.028	
N	2.720	2.920	0.107	0.115	
N1	1.227	1.427	0.048	0.056	

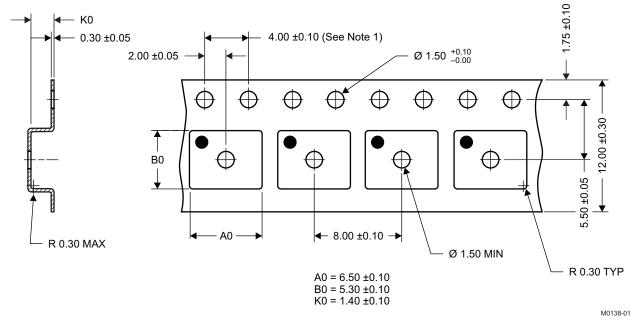




DIM	MILLIM	ETERS	INC	HES		
DIN	MIN	MAX	MIN	MAX		
F1	6.205	6.305	0.244	0.248		
F2	4.460	4.560	0.176	0.180		
F3	4.460	4.560	0.176	0.180		
F4	0.650	0.700	0.026	0.028		
F5	0.620	0.670	0.024	0.026		
F6	0.630	0.680	0.025	0.027		
F7	0.700	0.800	0.028	0.031		
F8	0.650	0.700	0.026	0.028		
F9	0.620	0.670	0.024	0.026		
F10	4.900	5.000	0.193	0.197		
F11	4.460	4.560	0.176	0.180		

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5C Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. Thickness: 0.30 ± 0.05 mm
- 6. MSL1 260°C (IR and convection) PbF reflow compatible



REVISION HISTORY

Changes from Original (October 2009) to Revision A	Page
Changed the device From: Procuct Preview To: Production	1
 Changed Application - From: Optimized for Control FET ApplicationsTo: Optimized for Synchronous FET Applications 	
Changed the pinout illustration.	1
Changed the Q5C Package Dimensions illustration	6
Changes from Revision A (December 2009) to Revision B	Page
 Changed the ABSOLUTE MAXIMUM RATINGS table, I_D - Continuous Drain Current value From: 30A To 	o: 31A 1
 Changed Note 1 of the ABSOLUTE MAXIMUM RATINGS table From: Typical R_{0JA} = 41°C To: Typical R 	_{θJA} = 40°C 1
 Changed Figure 1 - From: Typical R_{θJA} = 98°C/W To: Typical R_{θJA} = 94°C/W 	3
 Changed Figure 10 - From: Typical R_{θJA} = 98°C/W To: Typical R_{θJA} = 94°C/W 	5
Changed Figure 11 - X axis values	
Changes from Revision B (January 2010) to Revision C	Page
Changed the labels on the Bottom View pinout image	1
Changes from Revision C (February 2010) to Revision D	Page
Deleted the Package Marking Information section	7

PACKAGE MATERIALS INFORMATION

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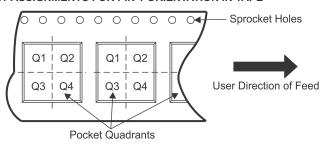
TAPE AND REEL INFORMATION





		Dimension designed to accommodate the component width
		Dimension designed to accommodate the component length
		Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
ľ	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16407Q5C	VSON- CLIP	DQU	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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*All dimensions are nominal

ĺ	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
	CSD16407Q5C	VSON-CLIP	DQU	8	2500	335.0	335.0	32.0	

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